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	Reg. No. :	
	Question Paper Code: 52937	
	B.E./B.Tech. DEGREE EXAMINATIONS, APRIL/MAY 2019.	
	Seventh/Eighth Semester	
	Electrical and Electronics Engineering	
	EE 6007 — MICRO ELECTRO MECHANICAL SYSTEMS	
	(Regulation 2013)	
	Common to Electronics and Instrumentation Engineering/ Instrumentation and Control Engineering/Mechanical Engineering.,/Robotics and Automation Engineering, Mechatronics Engineering)	
(	Also Common to: PTEE 6007 – Micro Electro Mechanical System for B.E. (Part- Time) – Sixth Semester – Electrical and Electronics Engineering – Seventh Semester – Mechanical engineering – Regulation 2014)	
Tir	ne : Three hours Maximum : 100 marks	
	Answer ALL questions.	
	PART A — $(10 \times 2 = 20 \text{ marks})$	
1.	What is the working principle of a piezo resistor to sense the pressure?	
2.	Which material is the most suitable one for high precision micro fabrication of sensors and actuators?	
3.	A piezoelectric crystal with piezoelectric coefficient $500 \times 10^{-12}$ m/V undergoes a mechanical strain equal to $125 \times 10^{-5}$ m/m. Calculate the induced voltage per meter in the crystal.	
4.	Why an electrostatic actuator is considered to be superior than an electromagnetic actuator?	
5.	Which MEMS sensor is deployed in the air-bags of car to sense the crash?	
6.	Write the working principle of a tactile sensor.	
7.	What type of etching will help to achieve high aspect ratio in MEMS fabrication process?	
8.	Which material is popularly used as the sacrificial layer in surface micro machining process?	
8.		

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9.	Wha	tare	the surface and wetting properties of polymers?	
10.	Can	liquid	l crystal polymer be used as a substrate? And why?	
			PART B — $(5 \times 13 = 65 \text{ marks})$	
11.	(a)	Writ	e a detailed technical note on the following:	
		(i)	Silicon crystal plane and its orientation.	
		(ii)	Longitudinal strain under pure bending.  Or	(13)
	(b)	A po surf	dysilicon cuboid with dimensions 2 cm $\times$ 2 cm $\times$ 3 cm ace. A force of 1 mN is applied on the top of surface. Fir	is placed on a
		(i)	the type of stress and	
		(ii)	the magnitude of stress induced in the direction of app	plied force.(13)
12.	(a)	Exp	ain in detail the operation of electrostatic mic opriate sketches.	romotor with (13)
			Or	
	(b)		orate on the working principle of an ink jet printer ba mal principle.	ased on electro (13)
13.	(a)	Exp	ain in detail how piezo resistor can be used to measure	
		(i)	pressure and	
		(ii)	inertia.	(13)
			Or	
	(b)	Disc	uss in detail how PZT is used as	
		(i)	acoustic sensor and	
		(ii)	ink jet actuator in the printer.	(13)
14.	(a)	Writ	te a detailed technical short note on :	
		(i)	Wet etching and	
		(ii)	MEMS device fabrication using 3D process.	(6+7)
			Or	
	(b)	(i)	A silicon wafer needs to be etched along < 111 > dire surface. Width of the mouth of the slot opening is 30 the slot is $10\mu$ m, from the mouth's surface.	ection from the $\mu$ m. Depth of
			Compute the width of the inner surface of the slot.	(6)
		(ii)	Explain the LIGA process and identify anyone device	that adopts it. (7)
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Flaharata hay namidana ia wasil ta hailil	(a)	15.	
Elaborate how parylene is used to build a pressure sensor. (13)	(a)	10.	
Or Discovering the State of the	(6)		
Discuss in detail about any one optical MEMS application. (13)	(b)		
PART C — (1 × 15 = 15 marks)			
(i) A thermal bimorph is initially flat where metal 1 is on the top and metal 2 is at the bottom. If its coefficient of thermal expansion $(\alpha)$ is such that $\alpha_1 < \alpha_2$ , then in what direction should it bend?	(a)	16.	
(ii) Barium titanate and Lead zirconate titanate has piezoelectric coefficient as 100 mN and 480 mN respectively. Comment which crystal will produce more mechanical strain due to the electric field.  (7+8)			
Or			
	(b)		
Analyse both the pull-in effect of parallel plate capacitor and the change in the distance between the plates. Hence, prove that the parallel plate capacitor can act as a switch under favourable operating conditions. (15)	(0)		
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